

An algorithm to model overclocking more accurately

IBIS Summit at DesignConEast 2003 Royal Plaza Hotel, Marlborough, MA June 23, 2003

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Outline

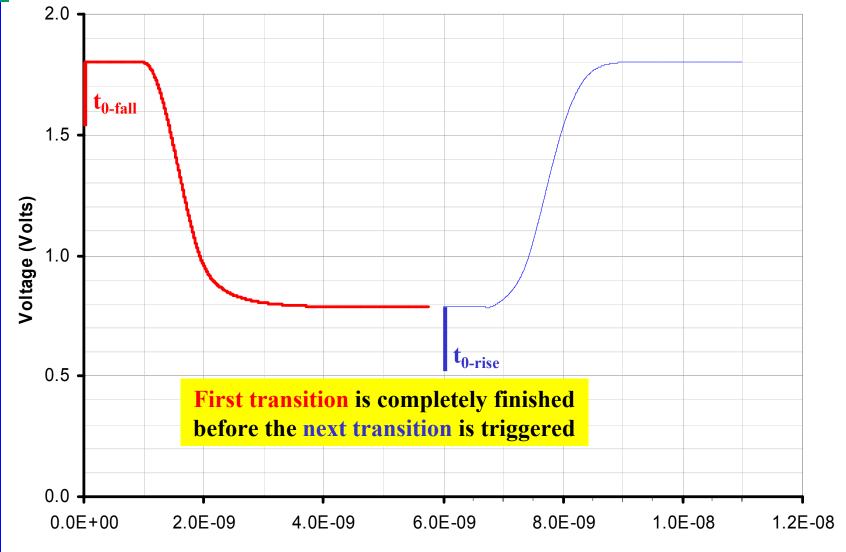
- Problem statement
- A possible algorithm idea (not good)
- A better algorithm idea
- SPICE waveforms to prove second idea





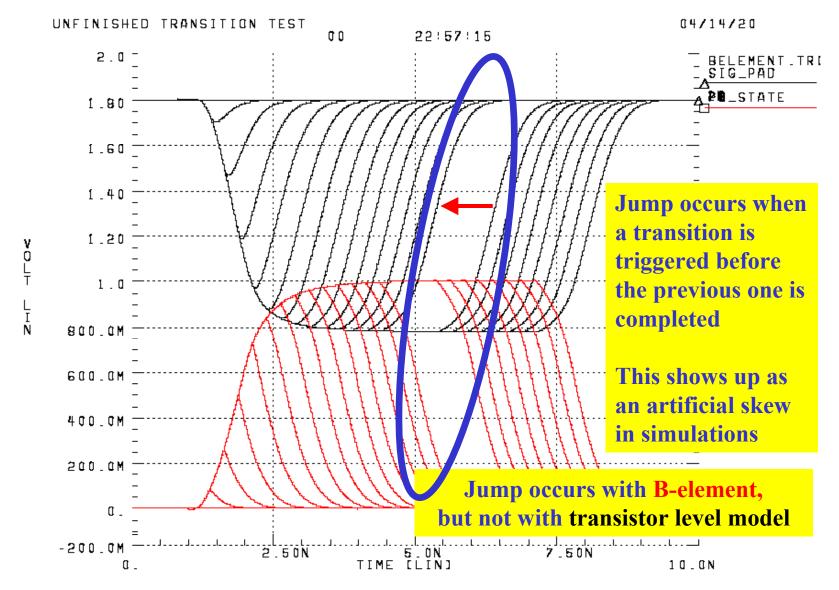
Normal operation







HSPICE's B-element in version 99.4





Disclaimer



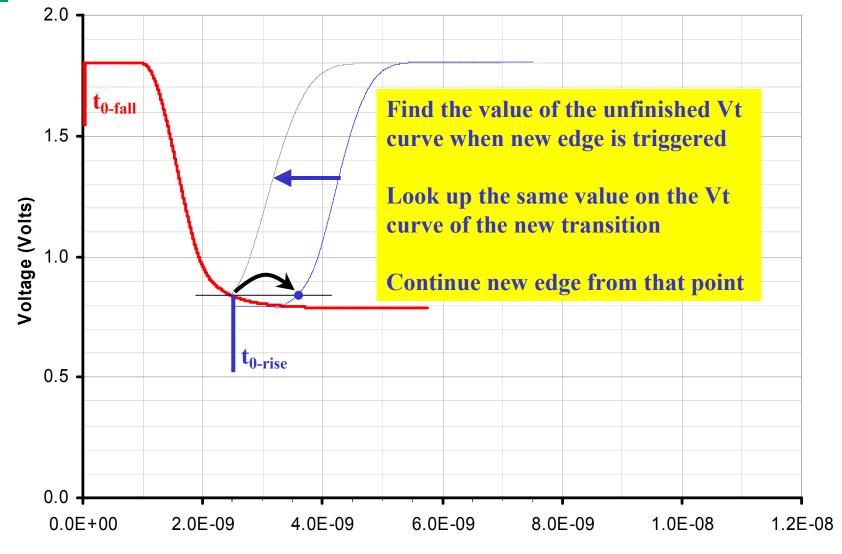
- Even though this problem was first discovered with HSPICE's B-element, this is not only an issue specific to HSPICE.
- The fundamental problem is that the IBIS specification was written with the assumption that a transition is always completed before a new transition begins.
- Since the IBIS specification does not address over-clocking, it is up to the tool vendor to deal with the situation when it arises.
- Each tool may have a different solution, some may seem to be correct (because they are not noticeable), but no one can really claim that they can reproduce the SPICE model's waveforms exactly when over-clocking occurs.





Conceptual explanation of the algorithm

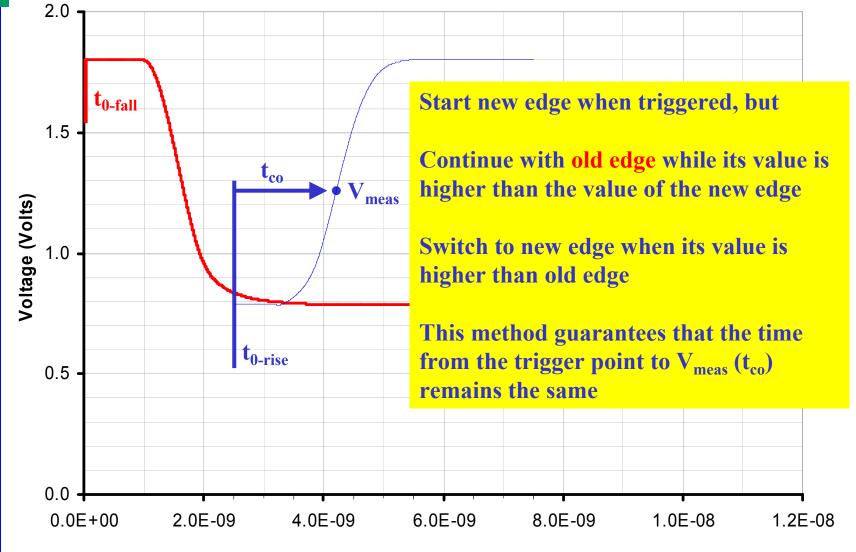


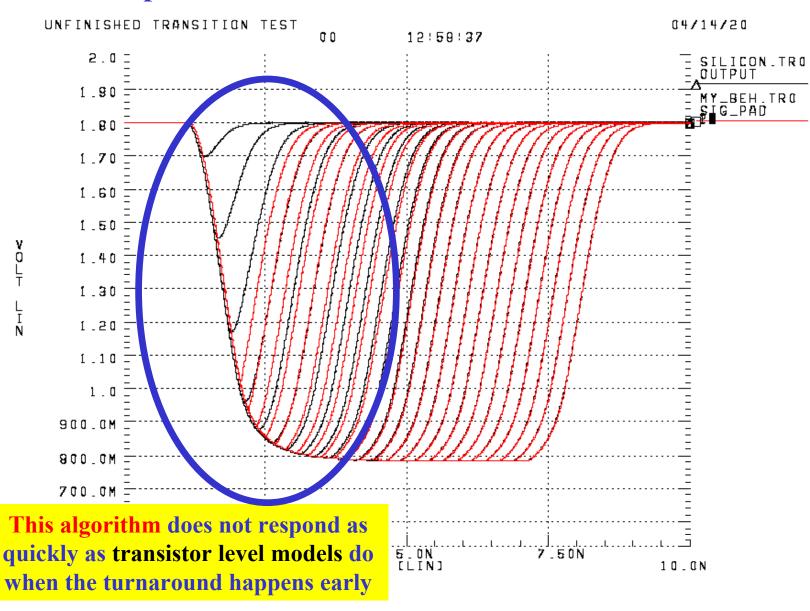




Arpad's first algorithm idea (don't implement it)







Arpad's first idea vs. transistor level model







Arpad's second algorithm idea

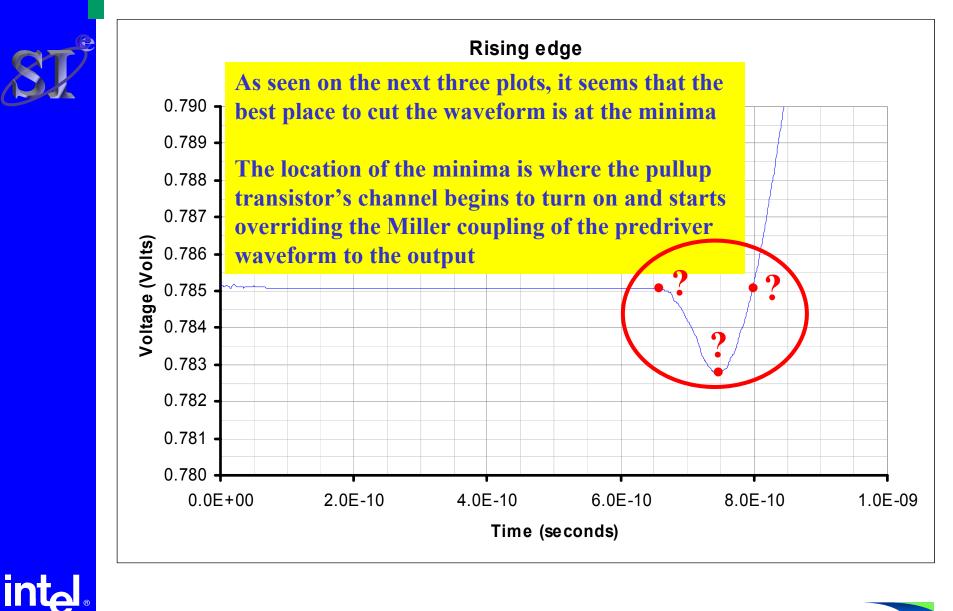
Delay t_{0-rise} **Replace the lead-in portion of the Vt curve with an ideal delay**

Use the original B-element algorithm with this modified Vt curve, but add a delay every time it is triggered

CPD

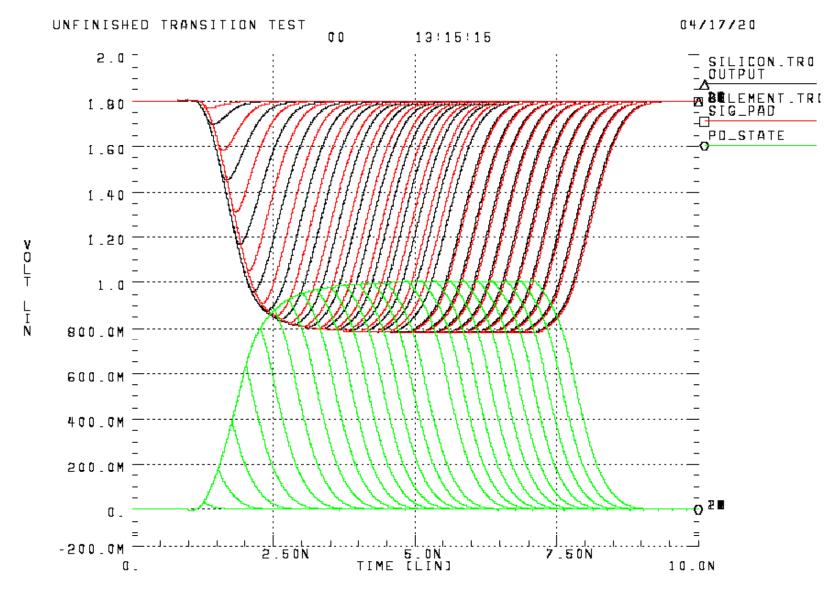


Where exactly should the Vt curve be cut?



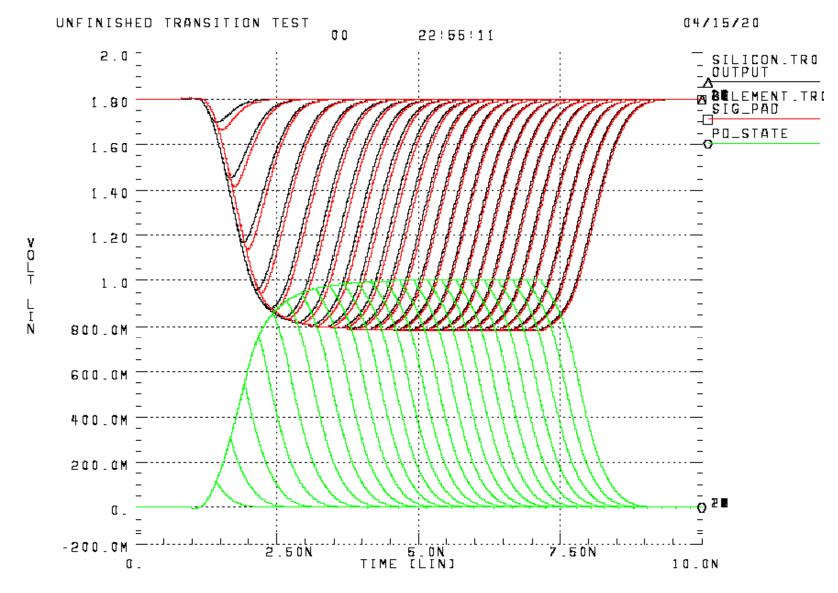
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Vt curve cut at left side





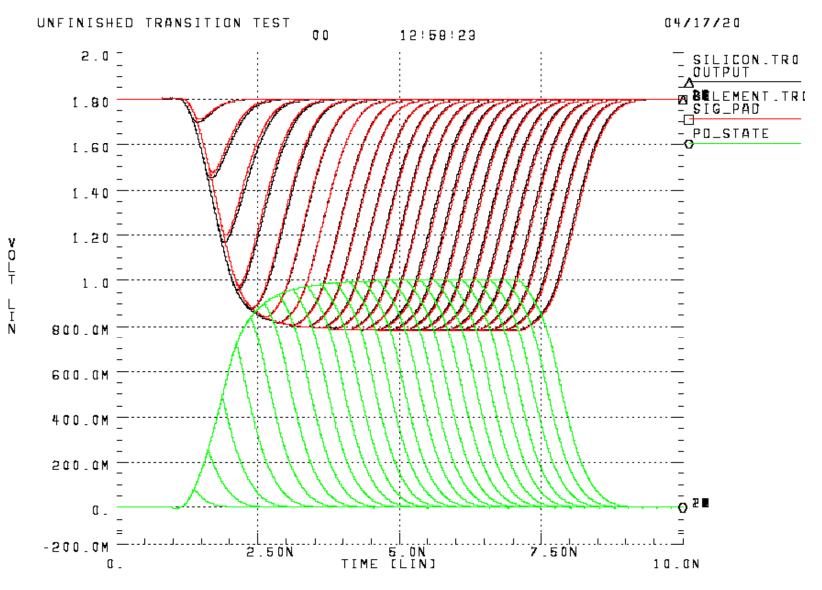
Vt curve cut at right side



SY



Vt curve cut at the minima yields best correlation

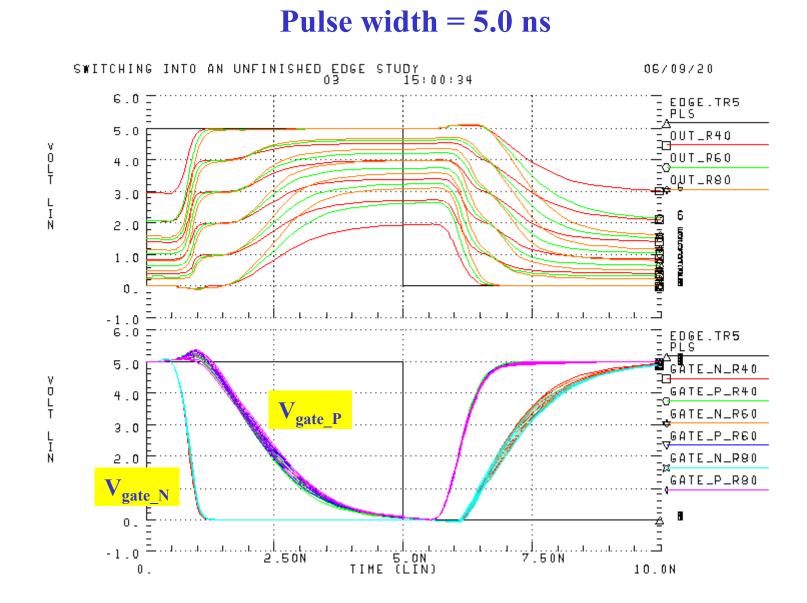


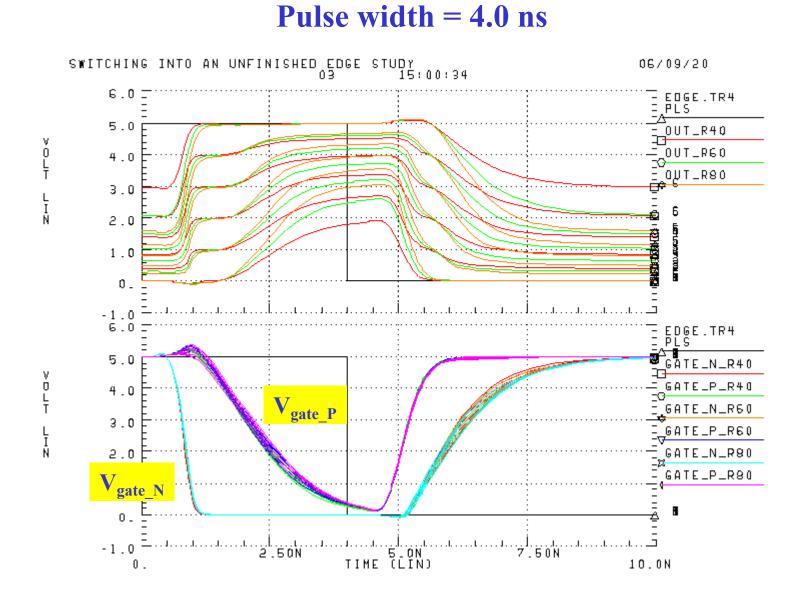
Looking inside the SPICE model for explanations

- We will look at two groups of six waveform sets.
 - Rising edge followed by a falling edge
 - Falling edge followed by a rising edge
- The second edge is brought closer to the first edge successively on each plot to watch the effects of over-clocking.
- The top plot shows waveforms on the output pad loaded by various $R_{fixture} V_{fixture}$ combinations.
 - 40, 60, 80 Ω
 - 0, 1, 2, 3, 4, 5 V
- The bottom plot shows the pre-driver output waveforms for the N and P-channel output transistors (gate voltages).
- Watching the output and pre-driver waveforms relative to the stimulus pulse we can make some observations.
 - There is a constant delay from the pulse to the pre-driver waveform
 - This explains the need for a delay element to keep the duration of the lead in portion of the Vt curves (i.e. internal delay of buffer)
 - The pre-driver waveforms turn around from the point they reached when over-clocking occurs
 - This explains the need for "turning around" on the Vt curves also



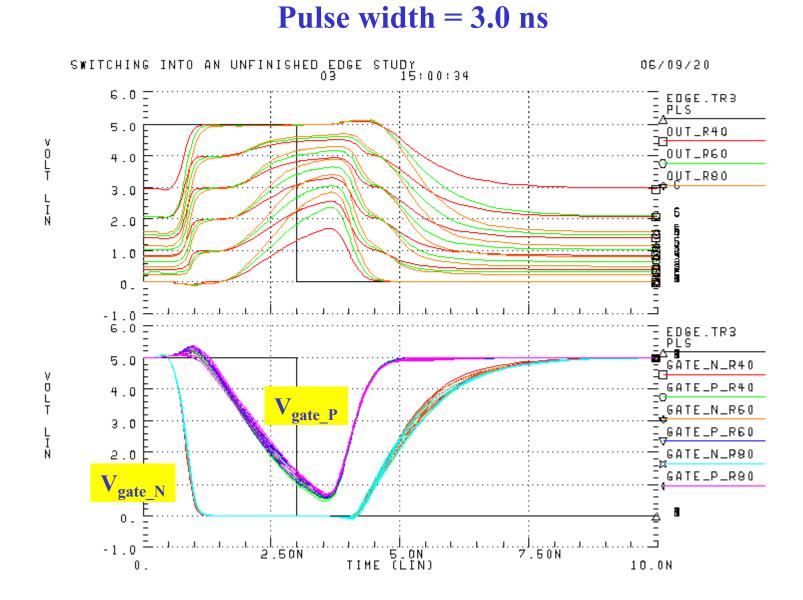


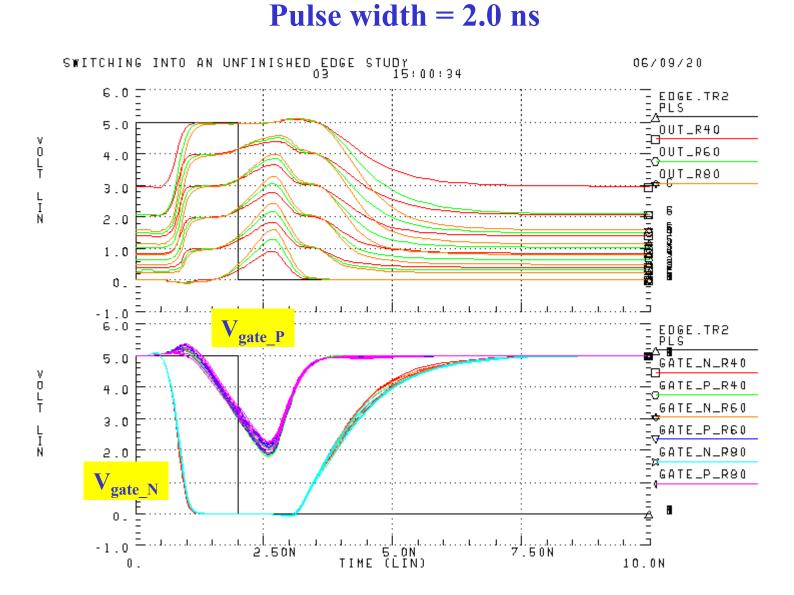


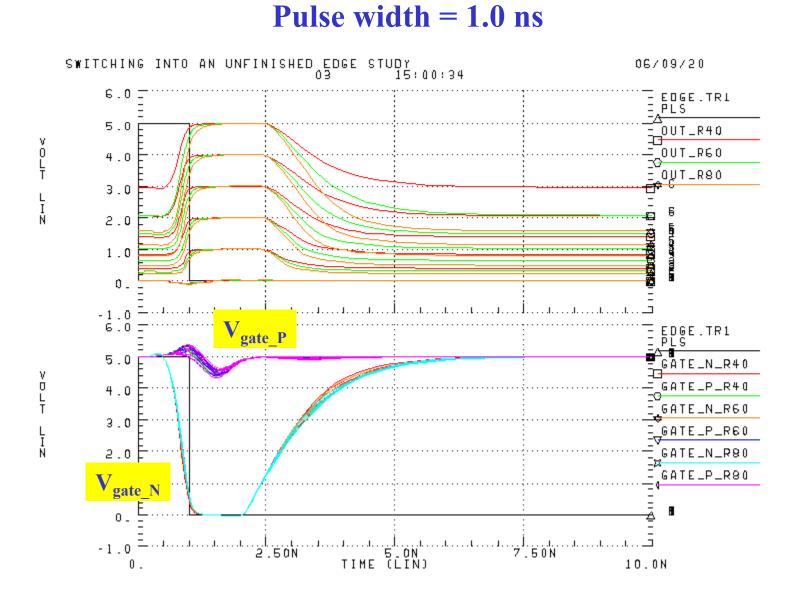


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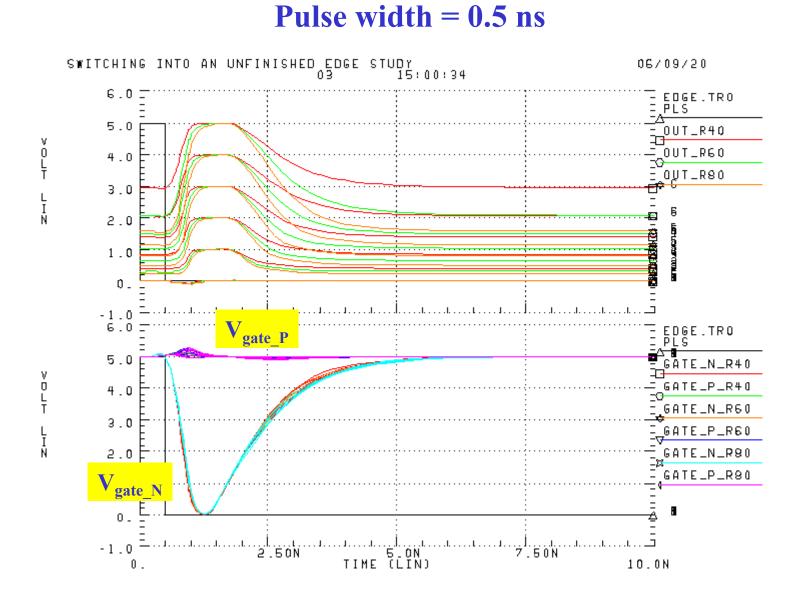














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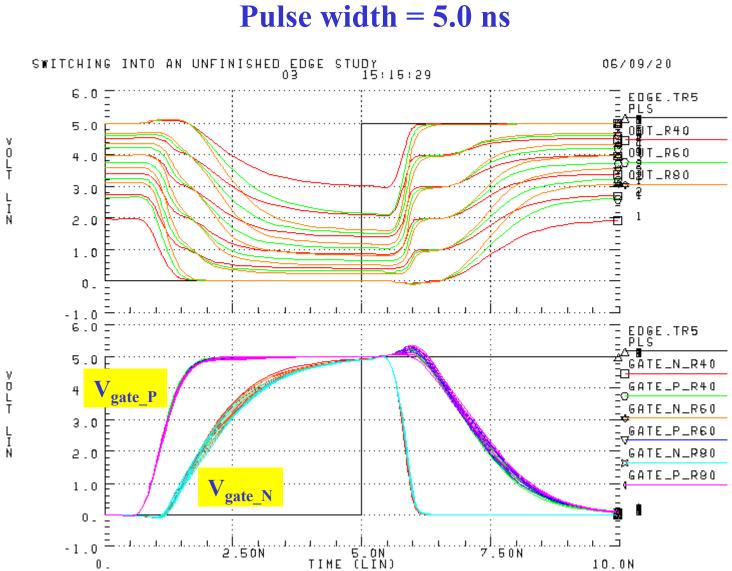




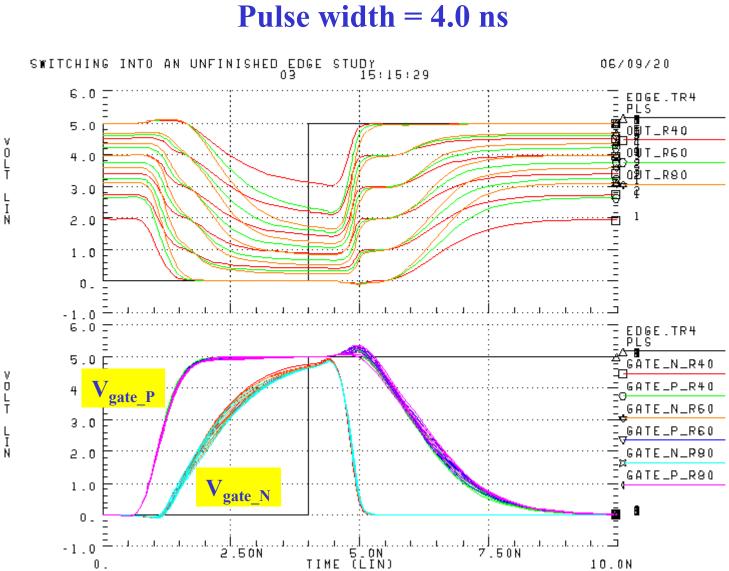
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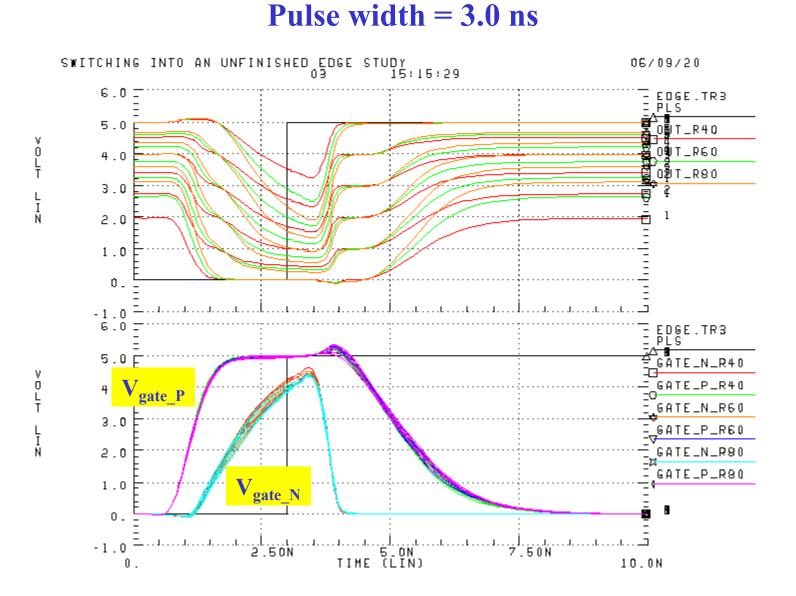


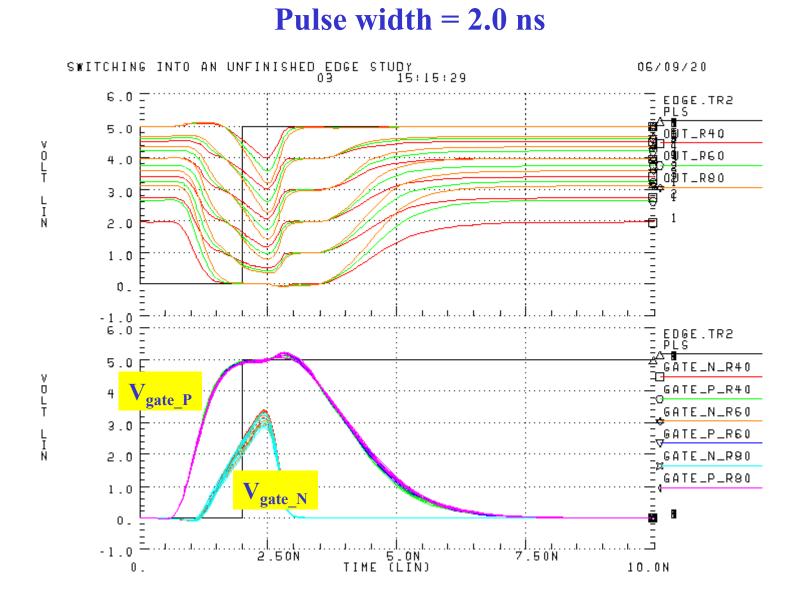






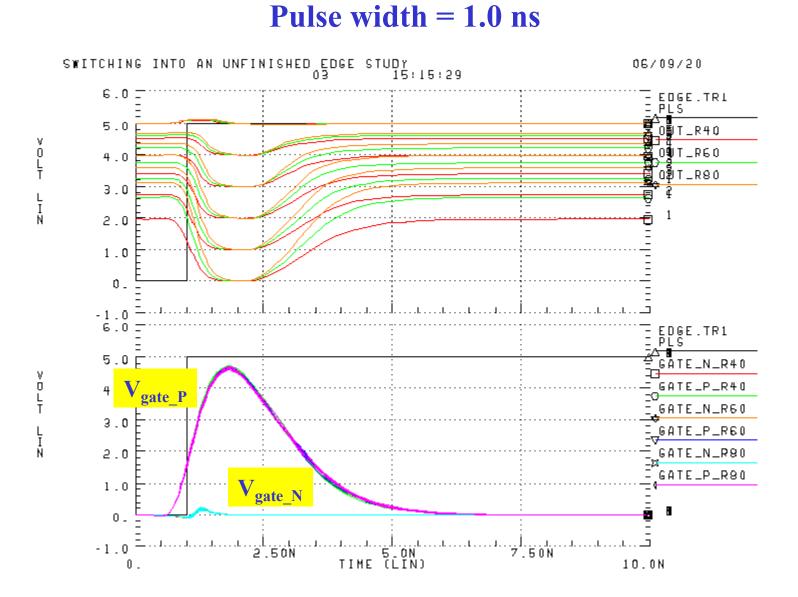




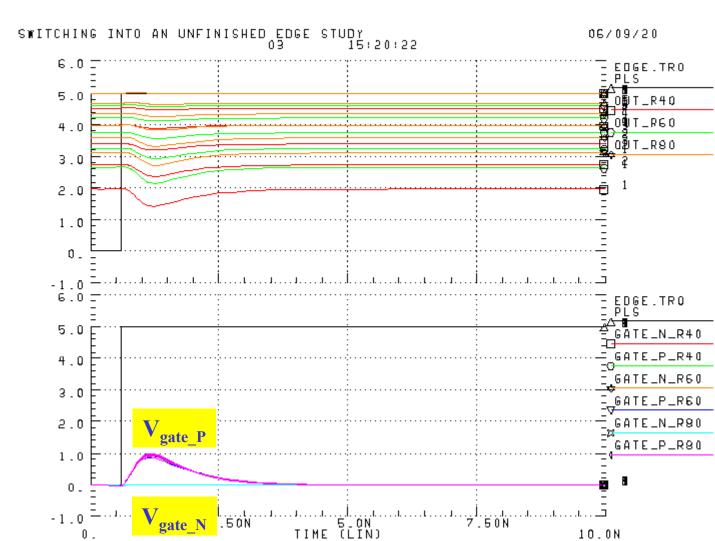








SV



Pulse width = 0.6 ns



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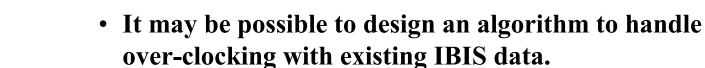
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Conclusions



- Looking at derivatives of the waveform could reveal the location where the output of the buffer really begins to switch
- The shape of the Vt curve may not always be usable for this purpose as a general solution
- A new parameter representing the internal delay(s) of a buffer may be a better way to do it.
 - Need to develop a technique for model makers to measure this number
 - Need to add a new keyword or sub-parameter to the IBIS specification associated with the waveforms



